

REMARKS

As indicated above, this is a Preliminary Amendment for the above-captioned patent application.

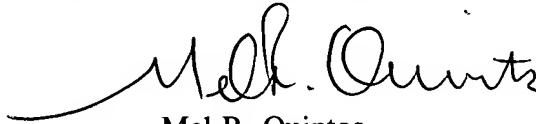
The specification has been amended in order to more particularly point out, and distinctly claim the subject matter to which the applicants regard as their invention.

The above amendments are believed to place the patent application in proper condition for examination. Early and favorable action is awaited.

In the event that this paper is not timely filed, applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees which may be due with respect to this paper, may be charged to Deposit Account No. 01-2340.

Respectfully submitted,

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Attachments: Version with markings to show changes made

VERSION WITH MARKINGS TO SHOW CHANGES MADE (10/014,407)

IN THE SPECIFICATION:

Paragraph beginning at page 11, line 14 has been amended as follows:

Referring to FIG. 1(a), first, a semiconductor substrate 9 consisting of high-resistivity N-type silicon single crystal is prepared. Here, a crystal with a resistivity of 20Ωcm or more, and less than or equal to 60Ωcm (less than or equal to $[2 \times 10^{14} \text{ cm}^{-3}]$ $2 \times 10^{14} / \text{cm}^3$ and greater than or equal to $[7 \times 10^{13} \text{ cm}^{-3}]$ $7 \times 10^{13} / \text{cm}^3$ in concentration conversions) was used as the semiconductor substrate 9.